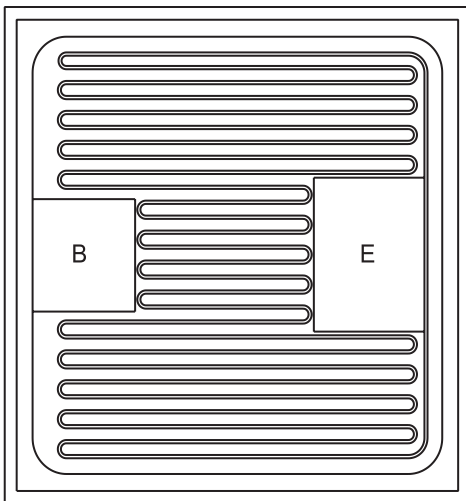


**PROCESS DETAILS**

Process	EPITAXIAL PLANAR
Die Size	41.3 x 41.3 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	9.5 x 9.2 MILS
Emitter Bonding Pad Area	12.8 x 10.2 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

**GEOMETRY**



BACKSIDE COLLECTOR

R0

**GROSS DIE PER 4 INCH WAFER**

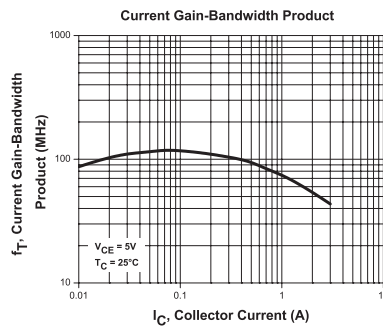
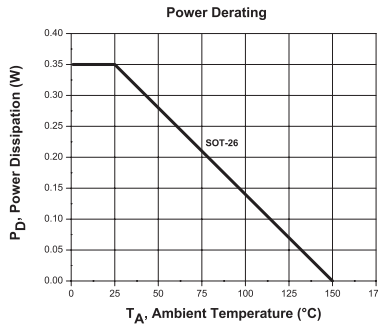
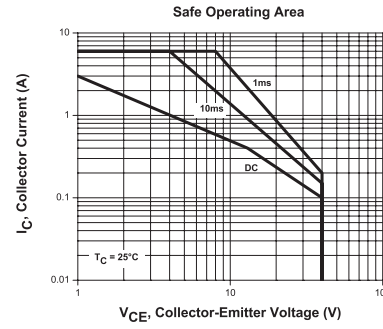
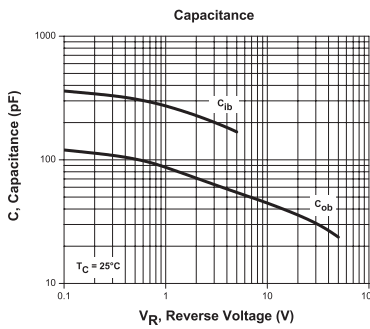
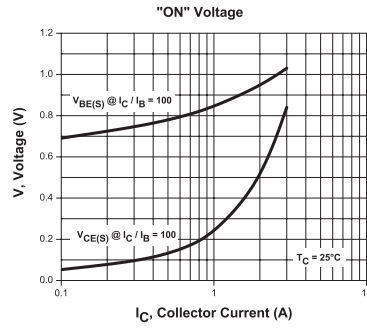
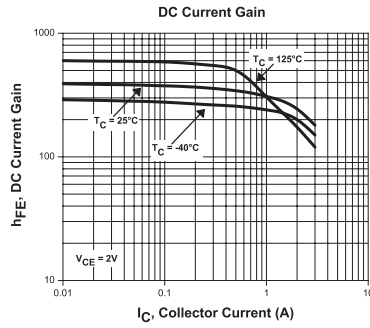
6,670

**PRINCIPAL DEVICE TYPES**

CMPT7090L  
CXT7090L  
CZT7090L  
CMXT7090L

145 Adams Avenue  
Hauppauge, NY 11788 USA  
Tel: (631) 435-1110  
Fax: (631) 435-1824  
www.centalsemi.com

R3 (23- August 2006)



145 Adams Avenue  
Hauppauge, NY 11788 USA  
Tel: (631) 435-1110  
Fax: (631) 435-1824  
www.centrasemi.com

R3 (23- August 2006)